

7. Semiconductor wafer (10) according to any one of the preceding claims, the group-IIIB silicide layer (5) having a (0001) surface orientation and/or being a $Y_{1-z}Sc_zSi_x$ layer with $0 \leq z \leq 1$.
8. Semiconductor wafer (10) according to any one of the preceding claims, the monocrystalline group-IIIA nitride layer (7, 8) being a coalesced film or a structured layer, especially comprising an array of rods, blocks, tips or pyramids.
9. Semiconductor wafer (10) according to any one of the preceding claims, the monocrystalline group-IIIA nitride layer (7, 8) being a monocrystalline $In_xAl_zGa_{1-(x+z)}N$ layer with $0 \leq x, z, (x+z) \leq 1$.
10. Semiconductor wafer (10) according to any one of the preceding claims, the monocrystalline group-IIIA nitride layer (7, 8) having a (0001) surface orientation.
11. Semiconductor wafer (10) according to any one of the preceding claims, the monocrystalline substrate wafer (1) being a Si(111) or Si(001) wafer.
12. Use of a semiconductor wafer (10) according to any one of the preceding claims as a substrate for producing light emitting elements, field effect transistors, or for microstructure printing.
13. Method for producing a semiconductor wafer (10) according to any one of the preceding claims, comprising the steps of:
 - providing a monocrystalline substrate wafer (1),
 - structuring the substrate wafer (1) to form tips (3) on its top surface,
 - covering the tips (3) in the given order with a group-IIIB silicide layer (5) and a group-IIIB nitride layer (6),
 - the group-IIIB silicide layer (5) having a thickness of not less than 5 nm,
 - covering the group-IIIB nitride layer (6) with a monocrystalline group-IIIA nitride layer (7, 8).